**Fig. 1**

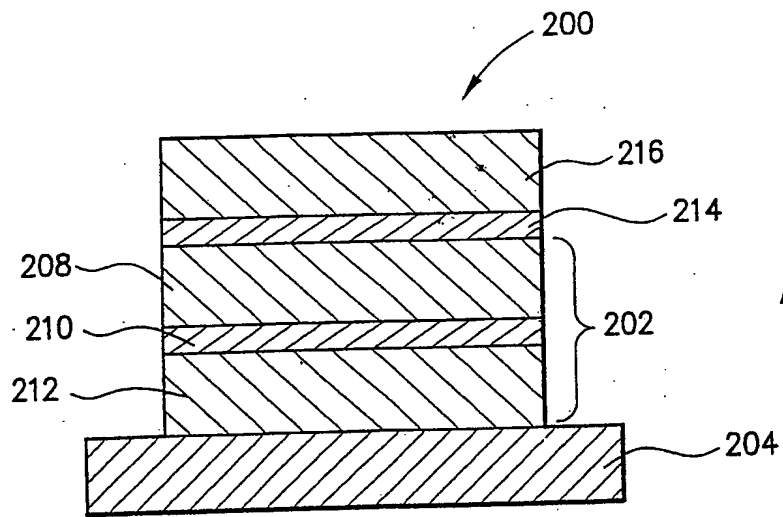


Fig. 2

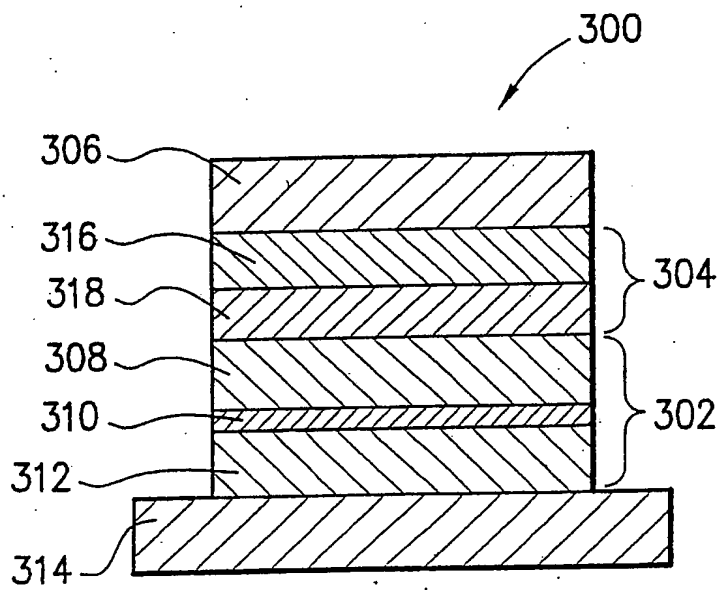


Fig. 3

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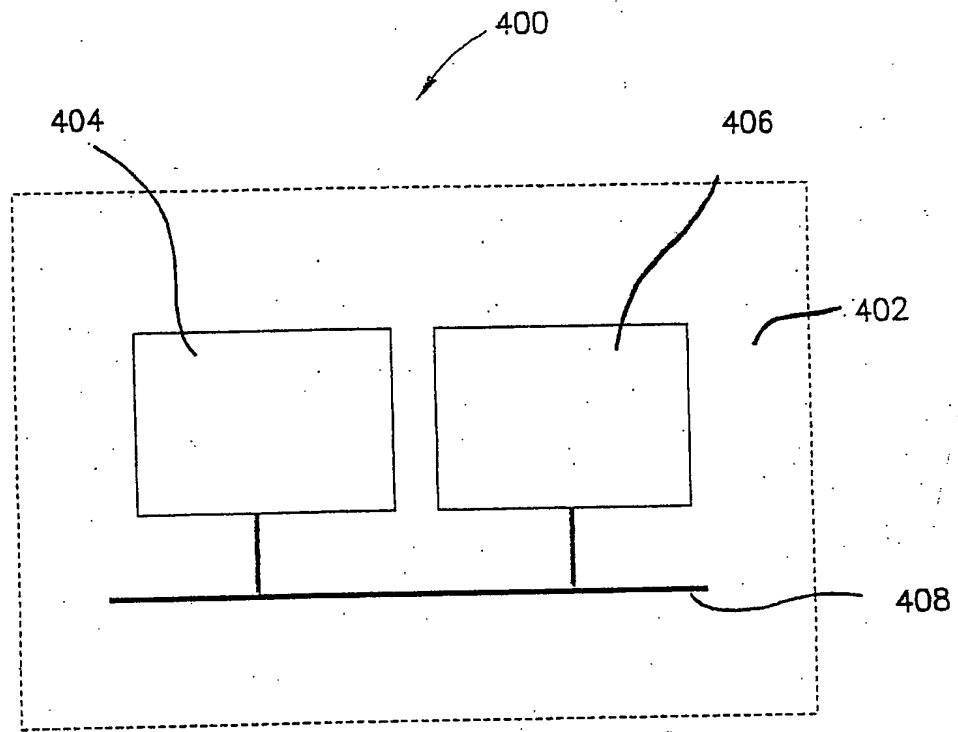


Fig. 4

500

HEATING MRAM CELLS OF AN ARRAY OF
MRAM CELLS, THE MRAM CELLS BEING
SWITCHABLE BETWEEN TWO STATES UNDER
THE INFLUENCE OF A MAGNETIC FIELD,
EACH MRAM CELL COMPRISING A
REFERENCE LAYER AND A DATA LAYER,
THE REFERENCE LAYER HAVING A LOWER
COERCIVITY THAN THE DATA LAYER

502

UTILIZING THE GENERATED HEAT TO
FACILITATE CELL STATE SWITCHING OF
MEMORY CELLS

504

Fig. 5